

MOS Fied Effect Transistor

2SJ212

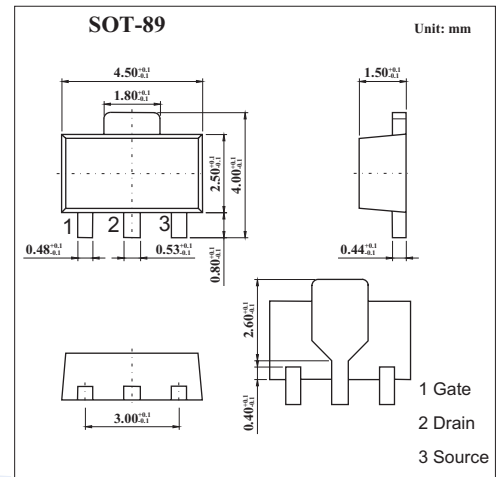
■ Features

- Directly driven by Ics having a 5V poer supply.

- Has low on-state resistance

$$R_{DS(on)}=4.0\ \Omega\ \text{MAX.}@V_{GS}=-4.0V, I_D=-0.3A$$

$$R_{DS(on)}=3.0\ \Omega\ \text{MAX.}@V_{GS}=-1.0V, I_D=-0.5A$$



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage V _{GS} =0	V _{DSS}	-60	V
Gate to source voltage V _{DS} =0	V _{GSS}	±20	V
Drain current (DC)	I _D	±500	m A
Drain current(pulse) *	I _D	±1.0	A
Power dissipation	P _D	2.0	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 ms; d ≥ 50%.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I _{DSS}	V _{DS} =-60V, V _{GS} =0			-10	μ A
Gate leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} =0			±10	μ A
Gate cut-off voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.0	-2.2	-3.0	V
Forward transfer admittance	Y _{fs}	V _{DS} =-5.0V, I _D =-0.3A	0.4	0.54		s
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =-4.0V, I _D =-0.3A		1.5	4.0	Ω
		V _{GS} =-10V, I _D =-0.5A		0.8	3.0	Ω
Input capacitance	C _{iss}	V _{DS} =-5.0V, V _{GS} =0, f=1MHZ		160		pF
Output capacitance	C _{oss}			100		pF
Reverse transfer capacitance	C _{rss}			25		pF
Turn-on delay time	t _{d(on)}	V _{GS(on)} =-4V, R _G =10 Ω, V _{DD} =-5V, I _D =--0.3A R _L =1.5 Ω		130		ns
Rise time	t _r			380		ns
Turn-off delay time	t _{d(off)}			95		ns
Fall time	t _f			140		ns

■ Marking

Marking	PD
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